

Features

- Trench Power MV MOSFET Technology
- Very Low On-Resistance RDS(ON)
- Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- · Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

Operating Junction Temperature Range : -55°C to +150°C

Storage Temperature Range: -55°C to +150°C

Thermal Resistance: 15°C/W Junction to Ambient(t≤10s)^(Note 2)

Thermal Resistance: 43°C/W Junction to Ambient(Steady-State)^(Note2,3)

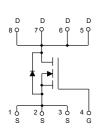
• Thermal Resistance: 1.47°C/W Junction to Case(Steady-State)

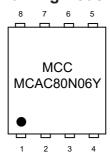
Parameter		Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	60	V	
Gate-Source Volltage	V _{GS}	±20	V	
Continuous Drain Current ^(Note 3)	T _C =25°C	1	80	Α
	T _C =100°C	l _D	58	Α
Pulsed Drain Current (Note 4	I _{DM}	320	Α	
Single Pulse Avalanche E	E _{AS}	450	mJ	
Total Power Dissipation ^(Note 2)	T _C =25°C	P _D	85	W
	T _C =100°C	' D	34	W

Note:

- 1.Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2.The Value of $R_{\theta JA}$ is Measured with the Device Mounted on $1in^2$ FR 4 Board with 2oz. Copper, in a Still Air Environment with T_A =25°C. The Power Dissipation P_{DSM} is Based on $R_{\theta JA}$ t ≤10s and the Maximum Allowed Junction Temperature of 150°C. The Value in Any Given Application Depends on the User's Specific Board Design.
- 3.The $R_{\theta JA}$ is the Sum of the Thermal Impedance from Junction to Case $R_{\theta JC}$ and Case to Ambient.
- 4. The Maximum Current Rating is Package Limited.
- 5. Single Pulse Width Limited by Junction Temperature T_{J(MAX)}=175°C.

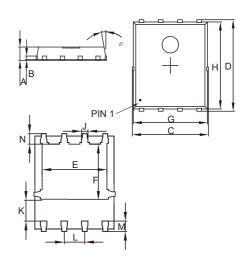
Internal Structure and Marking Code





N-CHANNEL MOSFET

DFN5060



DIMENSIONS						
DIM INCHES		HES	MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE	
Α	0.031	0.047	0.80	1.20		
В	0.010		0.254		TYP.	
С	0.193	0.222	4.90	5.64		
D	0.232	0.250	5.90	6.35		
Е	0.148	0.167	3.75	4.25		
F	0.126	0.154	3.20	3.92		
G	0.189	0.213	4.80	5.40		
Н	0.222	0.239	5.65	6.06		
K	0.045	0.059	1.15	1.50		
J	0.012	0.020	0.30	0.50		
L	0.046	0.054	1.17	1.37		
М	0.012	0.028	0.30	0.71		
N	0.016	0.028	0.40	0.71		
M	0.012	0.028	0.30	0.71		

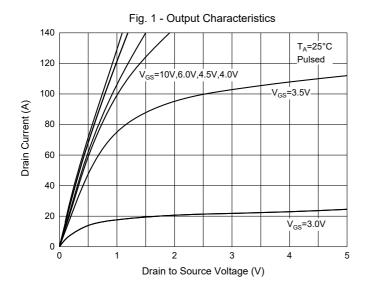


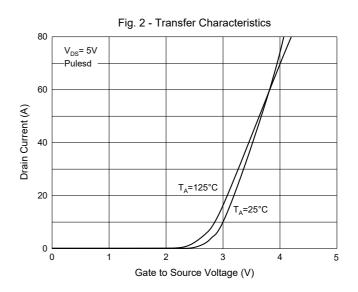
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

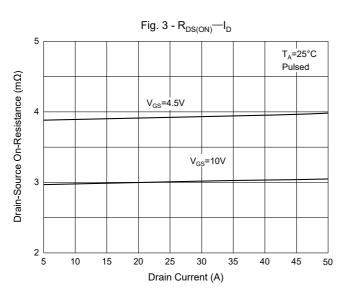
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics						1	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	60	65		V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1		
		V _{DS} =60V, V _{GS} =0V,T _J =55°C			5	μA	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_D=250\mu A$	1.1	1.7	2.5	V	
Drain-Source On-Resistance	Б	V _{GS} =10V, I _D =20A		3.0	4.2	mΩ	
	R _{DS(on)}	V _{GS} =4.5V, I _D =20A		3.9	5.2		
Forward Tranconductance	9 _{FS}	V _{DS} =5V, I _D =40A	30			S	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =40A		0.85	0.99	V	
Continuous Body Diode Current	Is				80	Α	
Dynamic Characteristics							
Input Capacitance	C _{iss}			3980		pF	
Output Capacitance	C _{oss}	V _{DS} =30V,V _{GS} =0V,f=1MHz		690			
Reverse Transfer Capacitance	C _{rss}			24			
Gate Resistance	R _g	V _{DS} =0V,V _{GS} =0V,f=1MHz		2.5		Ω	
Switching Characteristics							
Total Gate Charge	Q_g	V _{DS} =30V,V _{GS} =4.5V,I _D =40A		32			
Total Gate Charge	Qg			67			
Gate-Source Charge	Q _{gs}	V_{DS} =30V, V_{GS} =10V, I_{D} =40A		12		nC	
Gate-Drain Charge	Q _{gd}			8.5			
Reverse Recovery Chrage	Q _{rr}	I _F =I _S , di/dt=500A/μs		60			
Reverse Recovery Time	t _{rr}	1 _F -1 _S , αι/αι-300 <i>Α</i> /μS		48			
Turn-On Delay Time	t _{d(on)}			15			
Turn-On Rise Time	t _r	V_{GS} =10V, V_{DS} =15V, R_L =2.5 Ω ,		8		ns	
Turn-Off Delay Time	t _{d(off)}	R_{GEN} =3 Ω		48			
Turn-Off Fall Time	t _f			12			

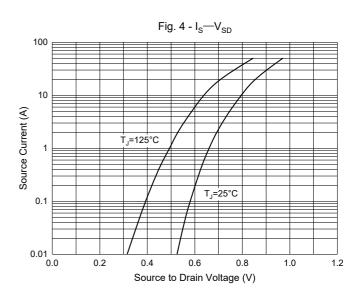


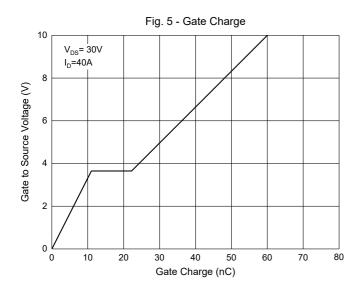
Curve Characteristics

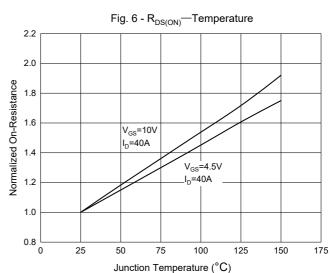














Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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